ESD in Silicon Integrated Circuits. 2nd Edition

Description:
- Examines the various methods available for circuit protection, including coverage of the newly developed ESD circuit protection schemes for VLSI circuits.
- Provides guidance on the implementation of circuit protection measures.
- Includes new sections on ESD design rules, layout approaches, package effects, and circuit concepts.
- Reviews the new Charged Device Model (CDM) test method and evaluates design requirements necessary for circuit protection.

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